The Instituto di Fotonica e Nanotecnologie (IFN) group of the Centro Nazionale di Ricerca (CNR) in Rome, Italy, hosted a combined SID-ME Spring meeting / 3rd International TFT Conference (ITC’07) on January 25-26, 2007. Guglielmo Fortunato, Senior Researcher at IFN-CNR, and his colleagues organized the meeting.

The two-day conference was divided into ten oral technical sessions, and one poster session. The technical sessions were “Flexible electronics 1+2”, “Poly-Si TFTs 1+2”, “Crystallization”, “Characterization and Modeling”, “OTFTs”, “Amorphous and Microcrystalline Silicon TFTs”, “New TFT Technologies”, and “Displays and Circuits”. The conference consisted of 82 accepted papers, of which 52 were oral presentations, and 30 posters. There were 110 attendees.

After a brief welcome by Guglielmo Fortunato and Eliav Haskal (Philips Research, FlexiDis coordinator), the lively conference began with many questions and answers, which remained the case throughout the entire two days. Of course, one highlight was the conference dinner, held in the restaurant roof garden “Les Etoiles” overlooking the Saint Peter’s Cathedral in Vatican City and the Castel Sant’Angelo in Rome, where an excellent Italian meal was enjoyed by the conference guests. Through the combination of the two conferences, the SID-ME chapter members were able to effectively exchange information and network with the mostly Asian attendees of the ITC’07. This unique chance was really appreciated by the entire conference!

Eliav Haskal
Conference summary

This conference comprised 82 contributions with two sets of parallel sessions. In view of this large number the usual SID-MEC Newsletter summary, with a few lines devoted to each paper, where an attempt is made to recall the main message or most important result, is omitted. Instead, the programme with titles and authors is included below.

ITC’07 / SID-MEC’07 Spring Meeting Conference programme
January 25

Session 1: Opening Session (9:00 - 9:15)

1.1: Welcome Address
G. Fortunato (CNR-IFN)
N. Fruehauf (Universität Stuttgart)
E. I. Haskal (Coordinator of FlexiDis Project - Philips Research, The Netherlands)

Session 2: Flexible electronics (1)
(9:15 - 10:35)(Session Chairman: E. Haskal)

2.1: 9:15-9:40 (Invited) Flexible active matrix electrophoretic displays made with a standard a-Si:H TFT technology using the EPLaRTM process
T. Kretz1, E. Chuiton1, G. Gomez1, F. Maze1, I. French2, I. J. Boerefijn3
1 Thales Avionics LCD, MOIRANS, France
2 Philips Research Laboratory, Redhill, UK
3 Philips Applied Technologies, High Tech Campus 7, 5656AE Eindhoven, The Netherlands

2.2: 9:40-10:05 (Invited) Flexible Thin-film Transistor for Display Application
C. C. Lee, Yung-Hui Yeh, Jia-Chong Ho
Process Technology Division, Display Technology Center, Industrial Technology Research Institute (ITRI)

2.3: 10:05-10:20 Printed organic transistors and plastic MEMS switches for a large-area flexible wireless power transmission sheet
T. Someya1, T. Sekitani1, M. Takamya2, Y. Noguchi1, S. Nakano1, T. Sakurai3
1 Quantum-Phase Electronics Center, School of Engineering, The University of Tokyo, Japan
2 VLSI Design and Education Center, The University of Tokyo, Japan
3 Center for Collaborative Research, The University of Tokyo, Japan

2.4: 10:20-10:35 Low-temperature polysilicon Thin Film Transistors on Polyimide substrates for electronics on plastic
A. Pecora, L. Maiolo, M. Cuscunà, D. Simeone, A. Minotti, L. Mariucci and G. Fortunato. Istituto di Fotonica e Nanotecnologie (IFN), CNR, Rome, Italy

10:35 - 10:50 Coffee Break

Session 3: Polysilicon TFTs (1)
(10:50 - 12:25) (Session Chairman: P. Migliorato)

3.1: 10:50-11:15 (Invited) Single-Grain Si TFTs and Circuits Fabricated through Advanced Excimer-Laser Crystallization
R. Ishihara, Vikas Rana, Ming He, Wim Metselaar and Kees Beenakker
Delft University of Technology, The Netherlands

3.2: 11:15-11:40 (Invited) Progress in Fabrication Processing of Thin Film Transistors
K. Yoshioka and T. Sameshima
Tokyo University of Agriculture and Technology, Tokyo, Japan

3.3: 11:40-11:55 High-Performance Double-Gate LTPS Thin Film Transistors Fabricated by Excimer Laser Irradiation
Chun-Chien Tsai1, Hsu-Hsin Chen1, Yao-Jen Lee2, Kai-Fong Wei1, Jyh-Liang Wong1, Bo-Ting Chen1, and Huang-Chung Cheng2
1 Department of Electronics Engineering and Institute of Electronics, National Chiao Tung University, Hsinchu, Taiwan
2 National Nano Device Laboratories, Hsinchu, Taiwan, ROC

3.4: 11:55-12:10 Fabrication of 3-Dimensionally Stacked Poly-Si TFT CMOS Inverter with High Quality Laser Crystallized Channel
Soon-Young Oh1, Chang-Geun Ahn1, Jong-Heon Yang1, Won-Ji Cho2, Woo-Hyun-Lee3, Hyun-Mo Koo1, Seong-Jae Lee1
1 Nano-Bio Electronic Devices Team, Electronics and Telecommunications Research Institute, Daejeon, KOREA
2 Eelectronic materials, Kwangwoon University, Seoul, KOREA
3.5: 12:10 - 12:25 High quality LTPS CMOS TFTs produced with a five mask process and only one ion implantation step
P. Schalberger, H. Bour, S. Kohlenbecker, E. Persidis, and N. Fruehauf
Chair of Display Technology, Universität Stuttgart, Germany

12:25 - 13:45 Lunch

Session 4: Flexible electronics (2)
(13:45 - 14:40) (Session Chairman: T. Noguchi)

4.1: 13:45 - 14:10 (Invited) Thin-film transistor backplanes on flexible polymer and steel foil substrates

4.2: 14:10 - 14:25 Near 100°C low temperature a-Si TFT array fabrication on flexible PES and PEN substrates
Ivan V. Nikulin, To Hyung Hwang, Hyung Il Jeon, Sang Il Kim, Nam Seok Roh, Seong Sik Shin
LCD R&D center, Samsung Electronics, Gyeonggi-Do, Korea

4.3: 14:25 - 14:40 Mechanical stability of poly-Si TFT on flexible metal foil
Jun Hyuk Cheon, Jung Ho Bae, and Jin Jang
Department of Information Display and Advanced Display Research Center, Kyung Hee University, Seoul, Korea

14:40 - 14:55 Coffee Break

Session 5a: Crystallization
(14:55 - 16:35)(Session Chairman: R. Ishihara)

5a.1: 14:55 - 15:20 (Invited) Location and Orientation Control of Si Thin-Film Grains Using Metal Nano-Imprint Seeding of
Laser Annealing
T. Asano, and G. Nakagawa
Department of Electronics, Kyushu University, Fukuoka, JAPAN

5a.2: 15:20 - 15:35 2D-projection-based method for forming uniform and high-quality poly-Si films via Sequential Lateral Solidification
Brandon A. Turk¹, Frank Simon² and Rainer Patzel²
1 Coherent, Inc., 5100 Patrick Henry Drive, Santa Clara, USA,
2 Coherent, GmbH, Göttingen, Germany

Tatsuya Okada, Seiichiro Higashi, Hirotaka Kaku, Takuya Yorimoto, Hideki Murakami and Seiichi Miyazaki
Department of Semiconductor Electronics and Integration Science
Graduate School of Advanced Sciences of Matter, Hiroshima University, Japan

5a.4: 15:50 - 16:05 Growth Rate Measurement of Lateral Grains in Silicon Film During Excimer Laser Annealing
Wenchang Yeh, Chunjun Zhuang, Dunyuan Ke
Department of Electronic Engineering, National Taiwan University of Science and Technology, Taipei, Taiwan, Republic of China

Session 5b: Characterization and modeling (14:55 - 16:40)(Session Chairman: Y. Uraoka)

5b.1 14:55 - 15:10 Hot carrier stress induced degradation of SLS ELA polysilicon TFTs - Effects of gate width variation and device orientation
G. P. Kontogiannopoulos¹, F.V. Farmakis¹, D.N. Kouvatsos², G. J. Papaioannou² and A.T. Voutsas³
1 Institute of Microelectronics, NCSR "Demokritos", Agia Paraskevi Attikis, Athens, Greece
2 Institute of Microelectronics, NCSR "Demokritos", Agia Paraskevi Attikis, Athens, Greece
3 LCD Process Technology Laboratory, Sharp Labs of America, Camas, WA, USA

5b.2: 15:10 - 15:25 Reliability for Joule effect in LTPS-TFTs with very thin gate oxide
H. Ueno, Y. Sugawara, Y. Uraoka and T. Fuyuki, T. Serikawa⁴
Graduate School of Materials Science, Nara Institute of Science and Technology, Nara, Japan

SID-Mid Europe Chapter Meeting
(Members only) (17:00)
Akiro Heya, Masahiko Sato and Naoto Matsuo
University of Hyogo, Japan

P1: Novel Surface Treatment of Plastic Substrate using Atomic Hydrogen for Flexible Displays
Akira Heya, Masahiko Sato and Naota Matsuo
University of Hyogo, Japan

P2: High-Performance Self-Aligned Bottom-Gate LTPS TFTs Fabricated by Excimer Laser Irradiation with...
P2: High-Performance Self-Aligned Bottom-Gate LTPS TFTs Fabricated by Excimer Laser Irradiation with Backside Exposure Photolithography
Department of Electronics Engineering and Institute of Electronics, National Chiao Tung University, Hsinchu, Taiwan
1 National Nano Device Laboratories, Hsinchu, Taiwan, ROC

P3: Improvement in Si/SiO2 properties using atmospheric pressure plasma
T. Miyamoto, Y. Sugawara, Y. Uraoka, T. Fuyuki, H. Kuroda, K. Takashima
Nara Institute of Science and Technology, Nara 630-0192, Japan

P4: Hafnium oxide deposited at room temperature by reactive RF magnetron sputtering from a metallic target for thin film transistors
Y.J. Choi, C. Ducati, Y. Fu, S. P. Speakman and A. J. Flewitt
1 Electrical Engineering Division, Cambridge University, Cambridge, UK
2 Department of Materials Science and Metallurgy, Cambridge University, Pembroke Street, Cambridge, UK
3 3T Technologies Ltd., 7, Essex, UK

P5: Fabricated Si Nanowire using Nanoimprint Method
Jin-Woo HAN, Dong-Hun KANG, Chul-Ho OK, Dae-Shik SEO
Department of Electrical and Electronic Engineering College of Engineering, Yonsei University, Seoul, Korea

P6: Low Temperature Formation of Si Oxide Thin Film for TFT by Reaction of Organosilicon polymer and Low Concentration Ozone Gas
Kensuke NISHIOKA, Kouichi TORIYABE and Susumu HORITA
Graduate School of Materials Science, Japan Advanced Institute of Science and Technology, Ishikawa, Japan

P7: CMOS LTPS-TFTs by using CW laser crystallization
Yang Duck Son, Kyung Dong Yang, Nam Kil Son, Eun-Hyun Kim, and Jin Jang
Department of Information Display and Advanced Display Research Center, Kyung Hee University, Korea

P8: High-Performance Poly-Si TFTs Fabricated by Floating Channel Crystallization Technology
Chia-Wen Chang, Jam-Wen Lee I, Che-Lun Chang, and Tan-Fu Lei
Department of Electronics Engineering and Institute of Electronics, National Chiao-Tung University, Hsin-Chu, Taiwan, R.O.C.
1 National Nano Device Laboratory, Hsin-Chu, Taiwan, R.O.C.

P9: Plane-to-Line Switching (PLS) Mode-Based Thin Film Transistor-Liquid Crystal Display (TFT-LCD) Adopting a Novel Concept of Process Architecture
Jae-Bok LEE, Chun-Ki YOU, Seong-Jun LEE, Hoon-Keen MIN and, Chi-Woo KIM
Mobile Display Process Development Team, LCD Business, Samsung Electronics Co., Ltd.San #24, Nongseo-dong, Kiheung-Ku, Yongin-City, Gyeonggi-Do, KOREA

P10: External Compensation of LTPS AMOLED Displays based on a Three TFTs Pixel Circuit
F. Pieralis, H. Baur, E. Persidis and N. FReuhauf, T. Marx
H. Schemmann, S. Weitbruch, P. Le Ray
1 Chair of Display Technology, Universität Stuttgart, 70569 Stuttgart, Germany
2 THOMSON Deutsche Thomson Brandt GmbH
3 THOMSON R&D France

P11: Leakage current-Free Pixel Structure Using a Shield Capacitor for Active-Matrix Display
Hyun-Sang Park, Jae-Hoon Lee and Min-Koo Han
School of Electrical Engineering (H50), Seoul National University, Seoul, Korea

P12: A New Amorphous Silicon Gate Driver with Stable Operation
Department of Information Display and Advanced Display Research Center, Kyung Hee University, Seou, Korea

P13: Two dimensional numerical simulation of low frequency noise in polysilicon thin film transistors
A. Boukhenoufa, C. Cordier, L. Pichon, B. Cretu
Groupe de Recherches en Informatique, Image, Automatique et Instrumentation de Caen (GREYC), CNRS UMR, ENSICAEN-Université de Caen, France
1 Groupe Microélectronique, IETR, UMR CNRS Rennes, France

P14: Electrical instability in self-aligned p-channel polysilicon TFTs related to oxide residual damage
M. Rapisarda, L. Mariucci, A. Valletta, A. Pecora and G. Fortunato
C. Caligiore, E. Fontana, S. Leonardi, F. Tramontana
1 CNR-IFN, Roma, Italy
2 CEA-LETI, Département IHS, 17 rue des Martyrs, Grenoble, France

P15: Hot carrier effects in p-channel polysilicon thin film transistors
P. Gaucci, L. Mariucci, A. Valletta, M. Cuscunà, L. Maiolo, A. Pecora, G. Fortunato, F. Templier
1 CNR-IFN, Roma, Italy
2 CEA-LETI, Département IHS, 17 rue des Martyrs, Grenoble, France.

P16: Effects of bias stress on low temperature polysilicon TFTs
D. Palumbo, S. Masala, P. Tassini, A. Rubinò, D. Della Sala
1 ENEA C. R. Portici, Portici (NA), Italy
2 DIIE, University of Salerno, Fisciano (SA), Italy
3 ENEA C. R. Casaccia, S. Maria di Galeria (Roma), Italy

P17: A New Poly-Si Thin-Film Transistor Nonvolatile Ge Nanocrystals Memory with High Programming / Erasing Efficiency
Po-Yi Kuo, Tien-Sheng Chao, Jyun-Siang Huang and Tan-Fu Lei
1 Department of Electronics Engineering and Institute of Electronics, National Chiao-Tung University, Hsinchu, Taiwan, R.O.C.
2 Department of Electrophysics, National Chiao-Tung University, Hsinchu, Taiwan, R.O.C.

P18: Characterization of advanced directional SLS ELA polysilicon TFTs -Dependence of device parameters on orientation and geometry-
D. C. Moschou, D. N. Kouvatsos, F.V. Farmakis, A.T. Voutsas
transient behavior of advanced excimer laser crystallized polysilicon thin film transistors
Michael A. Exarchos1, L.Michalas1, G.J.Papaioannou1, D.N.Kouvatso2, A.T.Voutsas3
1 National and Kapodistrian University of Athens (NKUA), Physics Department, Solid State Physics Section, Athens, Greece
2 National Center of Scientific Research (NCSR) "DEMOKRITOS", Institute of Microelectronics, Greece
3 SHARP Labs of America, LCD Process Technology Laboratory,Washington, USA
P20: DC Modeling of Single-Grain Si TFTs using BSIMSOI
Alessandro Baiano, Ryoichi Ishihara, Nobuo Karaki1 and Satoshi Inoue1, Wim Metseelaar and Kees Beenakker
Delft University of Technology, Feldmannweg 1-4, 2628 CT Delft, The Netherlands
1 Seiko Epson Cooperation, Nagano 399-0293, Japan
P21: Comparison of Defect Densities in Excimer Laser and Thermal Plasma Jet Crystallized Si Films
S. Higashi,T.Yorimoto,T. Okada, H. Kaku, H. Murakami and S. Miyazaki
Graduate School of Advanced Sciences of Matter, Hiroshima University, Japan
Y. Sugawara1, Y. Uraoka1, H. Yano1, T. Hayatama1 and T. Fuyuki1, A. Mimura2
1 Nara Institute of Science and Technology, Nara, Japan
2 National Institute of Advanced Industrial Science and Technology, Ibaraki, Japan
P23: OTFT Circuits on Plastic Manufactured by Self-Organized Process
S. H. Han, S. H. Lee, Y. R. Son, K. J. Lee, G. S. Cho, W. S. Kim, D. J. Choo2 and J.Jang
Department of Information Display Research Center Kyung Hee University, Hoegi-dong 1, Seoul, Korea
P24: Soluble Anthracene Oligomers Containing Thiophene Derivatives for Organic Thin Film Transistors
Jong-Hwa Park, Young Kwon Jung, Taek Ahn I, Mi Hye Yi, Hong-Ku Shim
Department of Chemistry and School of Molecular Science, Korea Advanced Institute of Science and Technology, Yuseong-Gu, Daejeon, Republic of Korea
1 Polymeric Nanomaterials Laboratory, Korea Research Institute of Chemical Technology,Yuseong-gu, Daejeon , Republic of Korea
P25: Study for characteristics of spin on dihexylsexithiophene thin film transistor
Jae-Hong Kwon1, Jung-Hoon Seo1, Dong Hoon Choi2, Yun-Hi Lee3, and Byeong-Kwan Ju1
1 Display and Nanosystem lab., School of Electrical Engineering, College of Engineering, Korea University, Korea
2 Functional Polymer Chemistry Lab., College of Science, Korea University, Anam-Dong, Seongbuk-Gu, Seoul, Korea
3 National Research Laboratory, Nano Device & Physics Lab., Department of Physics, Korea University, Korea
P26: Post-Treatment Effects on the Electrical Characteristics of Ink-jet Printed Trisopropylsilyl Pentacene Organic Thin-Film Transistors
Y.-H. Kim1, S.-M. Han2, J.-H. Lee3, J.-I. Han3 and M.-K. Han3
1 Information Display Research Center, Korea Electronics Technology Institute, Kyungji, Korea
2 School of Electric Engineering and Computer Science, Seoul National University, Seoul, Korea
P27: Insulator Passivation of Organic Thin-Film Transistor for Improving Device Performance
J.H. Seo, I.H. Kwon, K.S. Seo1 and B.K. Ju2
1 Convergence & Components Laboratory (ICCL), Electronics and Telecommunications Research Institute (ETRI), Daejeon, 305-700, KOREA
2 Display and Nanosystem Laboratory, School of Electrical Engineering, Korea University, Seoul 136-701, Korea
P28: Improvement of threshold voltage stability with bottom-gate polymorphous silicon Thin Film Transistors
François TEMPLIER1, Maher OUDWAN1, Frederic SERMET1, Alexey ABRAMOV2,3 and Pere Roca i CABARROCAS1
1 CEA-LETI, DIHS,Grenoble, France
2 LIPCM, Ecole Polytechnique, CNRS, Palaiseau, France
3 A.Foffee Phys.-Technical Institute, St.-Petersburg, Russia
P29: P-type Microcrystalline Silicon for Thin Film Transistors
Y. Djeridane, V.D. Bui, A. Abramov, Y. Bannasieux, P. Roca i Cabarrocas
LIPCM CNRS Ecole polytechnique Palaiseau, France
P30: Reduction of off current in ITO-channel thin film transistor with ferroelectric (Bi,La)4Ti3O12 gate insulator
Eisuke Tokumitsu, Tomofumi Fujimura, Takashi Sato, Etsu Shin and Masaru Senoo
Precision and Intelligence Laboratory, Tokyo Institute of Technology, Yokohama, Japan
19:30 Banquet
January 26
Session 6a: O-TFTs
(8:30 - 10:30)(Session Chairman: N. Fruehauf)
6a.1: 8:30 - 8:55 (Invited) Optimisation of Organic Semiconductors for Flexible Display Backplanes
M. Coelle
Merck
6a.2: 8:55 - 9:20 (Invited) Organic Thin Film Transistors for Flexible Display Applications
S. Burns
Plastic Logic Limited, Cambridge, United Kingdom
J.Jang and Seung Hoon Han
Dept. of Information Display, Kyung Hee University, Korea
6a.4: 9:45 - 10:00 Effect of active layer thickness on electrical characteristics of pentacene TFTs with PMMA buffer layer
L. Mariucci1, D. Simeone1, S. Cipolloni1, L. Maiola1, A. Pecora1 and G. Fortunato1, S. Bratherton2
Session 6b: Amorphous and microcrystalline silicon TFTs
(8:30 - 9:55)(Session Chairman: M.K. Han)

6b.1: 8:30 - 8:55 (Invited) Critical Issues in Plasma Deposition of Microcrystalline Silicon Thin Film Transistors
P. Roca y Cabarrocas1, Yassine Djeridane1 and Alexey Abramov1,2
1 LPICM, Ecole Polytechnique, CNRS, Palaiseau, France
2 A.F.Ioffe Phys.-Technical Institute, St.-Petersburg, Russia

6b.2: 8:55 - 9:10 New structure of a-Si:H TFT for controlling backlight brightness
Se Hwan Kim1, Eung Bum Kim1, Hee Yeon Choi1, Dong Han Kang1, Won Hoon Park1, Jae Hwan Oh1, Moon Hyo Kang1, Ji Ho Hur1, Jung Woo Lee2, Jung Ryoul Choi2, Seung Hun Ahn3, Soon Won Hong2 and Jin Jang1
1 Advanced Display Research Center Kyung Hee University, Seoul, Korea
2 Technology Leaders & Innovators, Kyunggi-Do, Korea

6b.3: 9:10 - 9:25 All Hot Wire CVD TFTs with High Deposition Rate Silicon Nitride (3 nm/s)
R.E.I. Schropp, S. Nishizaki1, Z.S. Hauweling, V.Verlaan, C.H.M van der Werf1, H.Matsumura1
1 Utrecht University, Faculty of Science, Department of Physics and Astronomy, SID-Physics of Devices, Utrecht, the Netherlands
2 Japan Advanced Institute of Science and Technology (JAIST), Ishikawa, Japan

6b.4: 9:25 - 9:40 Influence of the deposition temperature on the performance of microcrystalline silicon thin film transistors
M. Oudwan, A. Abramov1, P. Roca y Cabarrocas1 and F. Templier
CEA-LETI, DIHS, Grenoble, France

6b.5: 9:40 - 9:55 Microcrystalline TFTs: VerilogA Modeling
O. Moustapha, V.D. Bui, Y. Bonniseaux, J.Y. Parey
Laboratoire de Physique des Interfaces et Couches Minces LPICM-Ecole Polytechnique, France

10:30 - 10:45 Coffee Break
Sessin 8: Displays and circuits
(14:00 - 15:10) (Session Chairman: F. Templier)

8.1: 14:00 - 14:25 (Invited) Novel Mobile TFT-LCDs Based on SLS Technology
Mobile Display Business Team, LCD Business, Samsung Electronics Co., LTD

8.2: 14:25 - 14:40 LTPS-TFT process for AMOLED-displays
E. Persidis, H. Baur, R. Hlawatsch, F. Pieralisi, P. Schalberger, N. Fruehauf
Chair of Display Technology, Universität Stuttgart, Germany

8.3: 14:40 - 14:55 A new LTPS-TFT pixel for AMOLED to suppress the hysteresis effect on OLED current by employing a reset voltage driving
Jae-Hoon Lee, Sang-Myeon Han, Sang-Geun Park, Yong-Hoon Kim and Min-Koo Han
School of Electrical Engineering #50, Seoul National University, Seoul, Korea

8.4: 14:55 - 15:10 Suppression of TFT leakage current effect on active matrix displays by employing a new circular Switch
Jae-Hoon Lee, Hyun-Sang Park, Sang-Myeon Han, and Min-Koo Han
School of Electrical Engineering Seoul National University, Seoul, Korea

9.1: 15:25 - 15:40 Grain Boundary characterisation in Sequentially Laterally Solidified Polycrystalline-Silicon Thin Film Transistors
A Valletta, A Bonfiglietti, M Rapisarda, L Mariucci, A Pecora, G Fortunato, and S D Brotherton
IFN-CNR, Via Cineto Romano 42, Roma 00156, Italy
*TFT Consultant, 12 Riverside, Forest Row, RH18 5HB, UK

9.2: 15:40 - 15:55 Low temperature poly-Si TFT Flash memory with Si nano crystal dot
Nara Institute of Science and Technology Nara, Japan
*NISSIN ELECTRIC CO., LTD. Kyoto, Japan

9.3: 15:55 - 16:10 Low-cost poly-Si TFT with non-laser crystallization of amorphous silicon
Advanced Display Research Center and Department of Information display, Kyung Hee University, Seoul, Korea
*Mobile Display Business Team, LCD Business, Samsung Electronics, Gyeonggi-Do, Korea

SID-MEC General Meeting
Eliav Haskal (Philips Research) chaired the SID-MEC general meeting, where the status of the chapter was reported, and the election of the officers of the SID-ME chapter for the coming period took place. Gerrit Oversluizen was abdicating as vice-chair. Armin Wedel (Fraunhofer IAP) was the nominated new vice-chair. The other officers volunteered to run for another term, and the proposed candidates were elected unanimously. The new Chapter committee is now composed as follows: Patrick Vandenberghhe (Chair), Armin Wedel (Vice-Chair), Herbert De Smet (Secretary), Jutta Rasp (Treasurer). SID-MEC membership: with 555 members in January 2007, the SID-ME chapter has lost 10% compared to January 2006. This is primarily due to the expiration of the Eurodisplay’05 memberships. Overall, the membership is fairly constant over a period of 3 years. SID-ME has 8.2% of all 6747 SID members and is now the third largest chapter, after Japan (1130) and Bay Area (585) and before Korea (525). The 110 participants of this joint SID-MEC’07 spring meeting/ITC’07 meeting show that SID-MEC meetings continue to attract a high attendance. Jutta Rasp could unfortunately not attend the meeting; hence the presentation of the financial status is postponed until the next general meeting.

Conference dinner
The SID-MEC/ITC’07 conference dinner event took place on the 25th evening at the Restaurant Roof Garden “Les Etoiles”. This restaurant offers a beautiful panorama over Rome with views of St Peter’s.

The view from this roof-garden restaurant near the Vatican was magnificent, and the menu was excellent. The restaurant was decorated with wonderful wall tapestry, elegant furniture and exclusive interior.
The banquet on the SID-MEC/ITC’07 conference offered the possibility to discuss the topics of the conference in a very family way.

**SID-ME Chapter Student Award**

Unfortunately, the award session was cancelled. The award committee decided not to grant this years award because the application number was low and their quality considered insufficient. One of the causes may be the early date of the meeting, and possibly also the awareness of this award in the SID-MEC community can be improved. We trust that this will be a one off case. SID-MEC will continue promotion of this event and next year’s award will be grant-

**Closing remarks**

Focused in topic but distributed with respect to the geographical and cultural origin of the participants this meetings atmosphere was creative and stimulating new experiences. The magic of ancient Rome added yet another success factor to the mix. Thus this joint event of the SID-ME chapter with ITC’07 turned out very successful with visitors already longing for the next chance to meet again.

**Coming Events:**

**Eurodisplay’07**

**Russian Academy of Sciences, Moscow,**

**17-20 September, 2007**


**SID MEC Spring’08 Meeting**

**13-14 March 2008,**

**Fraunhofer IOF, Jena, Germany**

Special Topics: Microdisplays, Applications, and Optics

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The SID-ME Chapter committee is now formed by:
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SID payment.
The SID annual membership fee amounts US$ 75. Please note that the membership is now a rolling membership, which means that it runs 12 months from the month in which the payment was made. For more information see the SID website www.sid.org.
We encourage our members to pay directly to SID-HQ in the USA, but if they want to pay to the ME-Chapter directly the annual fee should be EUR 70 with all bank fees covered by the member !
Please note that due to the change in the US dollar/Euro exchange rate SID-MEC has re-evaluated the membership fee. In case of direct payment to the SID-ME Chapter the payment in EURO should be done to
Account no.: 206 020 1104
at: Berliner Sparkasse, Berlin,Germany
Bank code: BLZ 100 500 00
Account name: Frank Rochow, SID-ME
Please indicate your name on the remittance papers.
The Newsletter.
If you want to place an article in the Newsletter, which is interesting for the European display society, please send it to:
G. Oversluizen, fax: +31 40 274 6321,
E-mail: gerrit.oversluizen@philips.com
SID-ME Chapter Student Award

Call for SID-ME Chapter Student Award

The SID-ME Chapter Student Award is given for an outstanding scientific or technical achievement in, or contribution to, research on information display. The applicant is a student at a university/institute in the SID-ME region. The award amounts to 1500 Euro, with the obligation to present the contribution at the SID-MEC meeting where the award is presented. The conference fee is waived. The applicant must be a member of SID. For information on student membership, see below. The application deadline for the Spring’08 meeting in Jena is February 1, 2008

Application for SID-ME Chapter Student Award

Name:_________________________________________________________________________________________________

SID Membership No.:___________________________________________________________________________________

Institute/University: _____________________________________________________________________________________

Address: _________________________________________________________________________________________________

Title of contribution: ______________________________________________________________________________________

Abstract (100-150 words):
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References (SID-ME member):
__________________________________________________________________________

The application should be submitted to the award committee consisting of:
Prof. Dr.-Ing. N. Frühauf, Universität Stuttgart, Allmandring 3B, D-70550 Stuttgart-Vaihingen, Germany, Tel.: +49 711 685 6922, Fax: +49 711 685 6924.
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SID Student Membership:

At http://www.sid.org you find information on SID student membership. Note the favourable offer of $5.00 per year for student members.